

ABSTRACT OF THE DISCLOSURE

A semiconductor device and a method for manufacturing the semiconductor device capable of reducing a short channel effect are provided.

The semiconductor device is made up of a pair of impurity regions for a source and a drain formed on a semiconductor substrate, a gate having a gate electrode used to control a drain current and side walls formed on both sides of the gate electrode and a pair of electrode members formed on both sides of the semiconductor substrate and in a manner to be in contact with the side walls. As impurity regions, there are provided first impurity regions formed by thermal diffusion of impurities from each of the electrode members and second impurity regions each having a thickness being smaller than that of the first impurity region and extending below the gate electrode, which are formed by thermal diffusion of impurities from the side walls.